

Philips Semiconductors

Objective specification

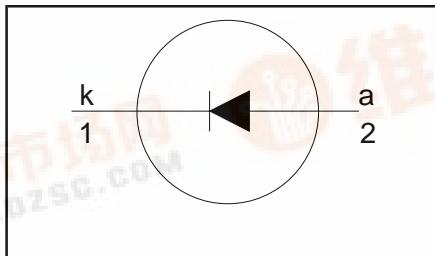
Rectifier diode  
fast, high-voltage

BY359DX-1500

## FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Isolated mounting tab

## SYMBOL



## QUICK REFERENCE DATA

$V_R = 1500 \text{ V}$   
 $V_F \leq 1.5 \text{ V}$   
 $I_{F(AV)} = 10 \text{ A}$   
 $I_{F(SM)} \leq 60 \text{ A}$   
 $t_{fr} \leq 600 \text{ ns}$

## GENERAL DESCRIPTION

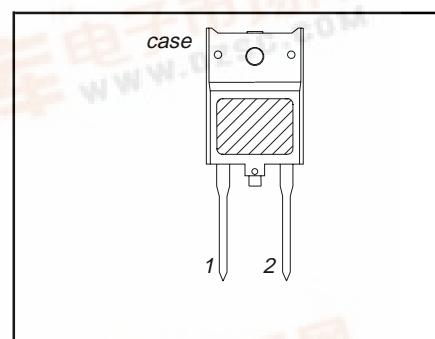
Glass-passivated double diffused rectifier diode featuring low forward voltage drop, fast reverse recovery and soft recovery characteristic. The device is intended for use in TV receivers, series resonant switched mode power supplies and other high voltage circuits.

The BY359DX series is supplied in the conventional leaded SOD117 package.

## PINNING

PIN	DESCRIPTION
1	cathode
2	anode
tab	isolated

## SOD117



## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{RSM}$	Peak non-repetitive reverse voltage		-	1500	V
$V_{RRM}$	Peak repetitive reverse voltage		-	1500	V
$V_{RWM}$	Crest working reverse voltage		-	1300	V
$I_{F(AV)}$	Average forward current	sinusoidal; $a = 1.57$ ; $T_{hs} = t_{bf}$	-	10	A
$I_{F(RMS)}$	RMS forward current		-	20	A
$I_{FRM}$	Peak repetitive forward current	sinusoidal; $a = 1.57$	-	60	A
$I_{FSM}$	Peak non-repetitive forward current	$t = 10 \text{ ms}$	-	60	A
$I^2t$	$I^2t$ for fusing	$t = 8.3 \text{ ms}$	-	66	A
$T_{stg}$	Storage temperature	half sine wave; $T_j = 150 \text{ }^\circ\text{C}$ prior to surge; with reapplied $V_{RWM(max)}$	-	18	$\text{A}^2\text{s}$
$T_j$	Operating junction temperature	$t = 10 \text{ ms}$	-40	150	$^\circ\text{C}$
			-	150	$^\circ\text{C}$

## ISOLATION LIMITING VALUE &amp; CHARACTERISTIC

$T_{hs} = 25 \text{ }^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{isol}$	R.M.S. isolation voltage from both terminals to external heatsink	$f = 50-60 \text{ Hz}$ ; sinusoidal waveform; R.H. $\leq 65\%$ ; clean and dustfree	-		2500	V
$C_{isol}$	Capacitance from both terminals to external heatsink	$f = 1 \text{ MHz}$	-	10	-	pF

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### THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Thermal resistance junction to heatsink	with heatsink compound	-	-	tbf	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	without heatsink compound in free air.	-	-	tbf	K/W

### STATIC CHARACTERISTICS

$T_j = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_F$	Forward voltage	$I_F = 20\text{ A}$	-	1.3	1.8	V
$I_R$	Reverse current	$I_F = 10\text{ A}; T_j = 150^\circ\text{C}$ $V_R = 1300\text{ V}$ $V_R = 1300\text{ V}; T_j = 100^\circ\text{C}$	-	1.00	1.5	V

### DYNAMIC CHARACTERISTICS

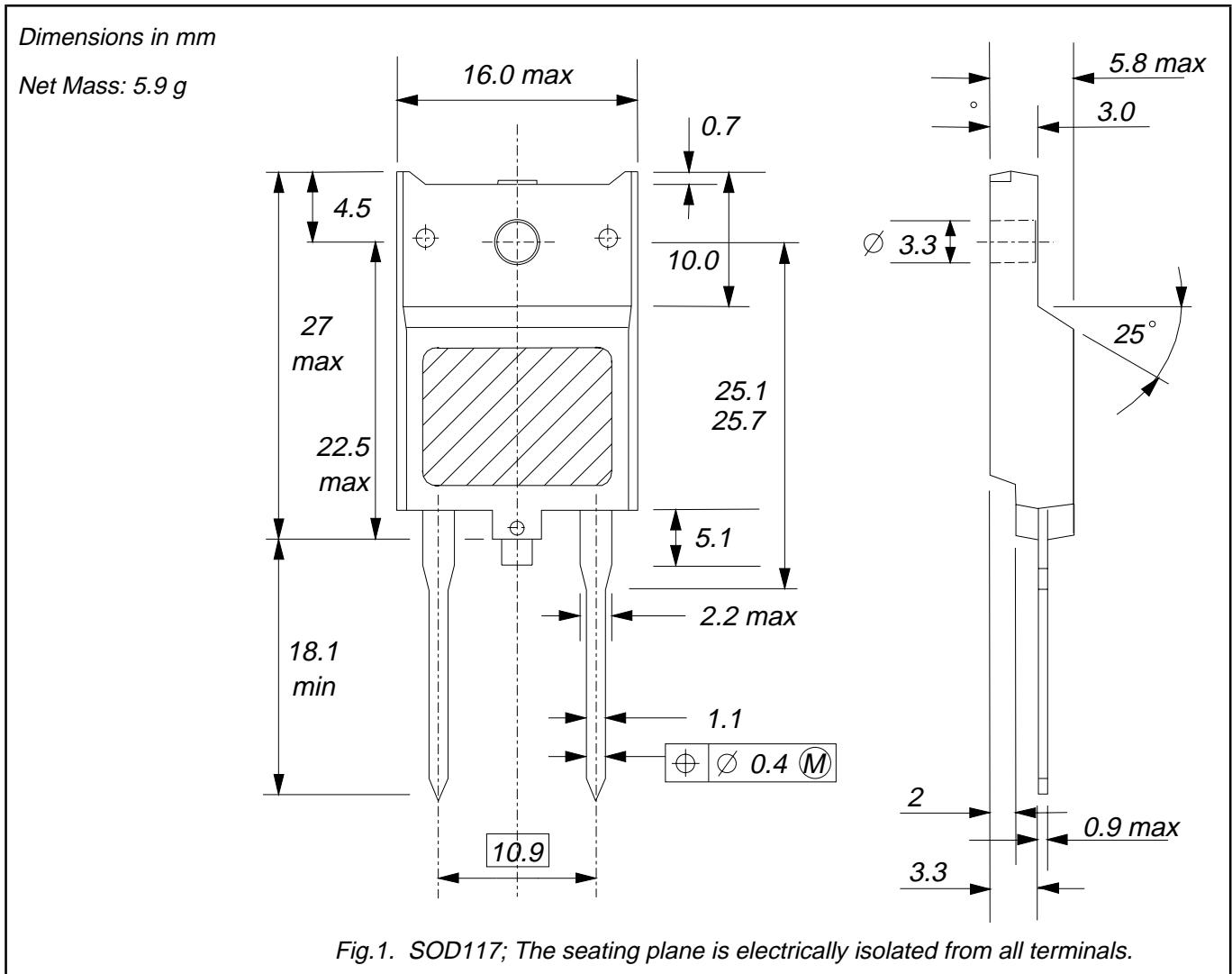
$T_j = 25^\circ\text{C}$  unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$t_{rr}$	Reverse recovery time	$I_F = 2\text{ A}; V_R \geq 30\text{ V}; -dI_F/dt = 20\text{ A}/\mu\text{s}$	-	0.47	0.6	$\mu\text{s}$
$Q_s$	Reverse recovery charge	$I_F = 2\text{ A}; V_R \geq 30\text{ V}; -dI_F/dt = 20\text{ A}/\mu\text{s}$	-	1.6	2.0	$\mu\text{C}$
$V_{fr}$	Peak forward recovery voltage	$I_F = 10\text{ A}; dI_F/dt = 30\text{ A}/\mu\text{s}$	-	11.0	-	V

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## MECHANICAL DATA



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## Notes

1. Refer to mounting instructions for F-pack envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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## DEFINITIONS

<b>Data sheet status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	
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